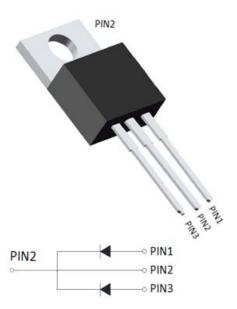




Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102 • Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR3060CT
Device marking code			MBR3060CT
Repetitive Peak Reverse Voltage	VRRM	٧	60
Average Rectified Output Current @60Hz sine wave, R-load, Tc(FIG.1)	IO	Α	30
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave,1 cycle, T _a =25°C	IFSM	Α	250
Current Squared Time @1ms≤t≤8.3ms Tj=25˚C	l²t	A ² s	260
Typical Junction capacitance @4V,1MHz	Cj	pF	600
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ +175
Junction Temperature	Тј	$^{\circ}$	-55 ~ +175

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR3060CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=15.0A	0.72
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM T _a =25℃	0.2
	IRRM2		VRM=VRRM T _a =125℃	50

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS



MBR3060CT

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER		SYMBOL	SYMBOL UNIT MBR3060	
Thermal Resistance	Between junction and case	R _{θJ-C}	°C /W	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR3060CT	Approximate 1.9	50	1000	5000	Tube

■Characteristics (Typical)

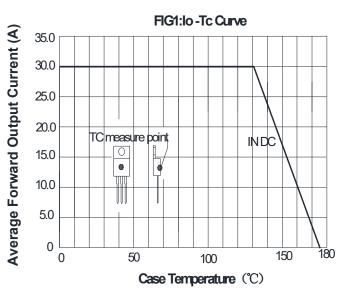
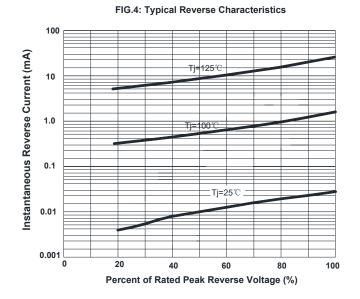


FIG2:Surge Forward Current Capability 300 Peak Forward Surge Current (A) 250 200 8.3ms Single Half Sine-Wave 150 JEDEC Method 100 50 0 2 10 50 100 **Number of Cycles**

FIG3: Forward Voltage

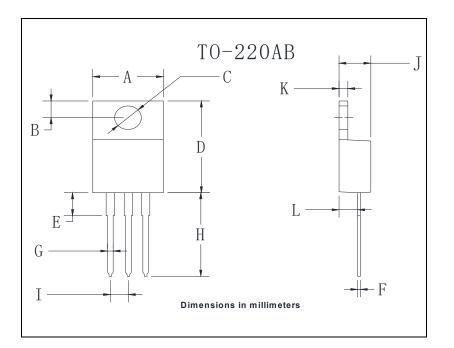
100
60
20
10
5.0
1.0
0.5
0.1
0.2
0.1
0.1
0.2
0.3
0.4
0.5
0.6
0.7
0.8
0.9
1.0
1.1
1.2
Instantaneous Forward Voltage (V)







■Outline Dimensions



TO-220AB				
Dim	Min	Max		
Α	9.95	10.35		
В	2.55	2.95		
С	3.8	4.0		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.4	13.9		
I	2.35	2.65		
J	4.38	4.78		
K	1.14	1.4		
L	2.37	2.79		



MBR3060CT

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